5 V ECL Differential Data and Clock D Flip-Flop

MC10EL52, MC100EL52

8
1

SOIC−8 NB
D SUFFIX
CASE 751−07

Description

The MC10EL/100EL52 is a differential data, differential clock D flip-flop with reset. The device is functionally equivalent to the E452 device with higher performance capabilities. With propagation delays and output transition times significantly faster than the E452, the EL52 is ideally suited for those applications which require the ultimate in AC performance.

Data enters the master portion of the flip-flop when the clock is LOW and is transferred to the slave, and thus the outputs, upon a positive transition of the clock. The differential clock inputs of the EL52 allow the device to also be used as a negative edge triggered device.

The EL52 employs input clamping circuitry so that under open input conditions (pulled down to V_{EE}) the outputs of the device will remain stable.

The 100 Series contains temperature compensation.

Features

- 365 ps Propagation Delay
- 2.0 GHz Toggle Frequency
- ESD Protection:
    - ♦ > 1 kV Human Body Model
    - ♦ > 100 V Machine Model
- PECL Mode Operating Range: $V_{CC} = 4.2$ V to 5.7 V with $V_{EE} = 0$ V
- NECL Mode Operating Range: $V_{CC} = 0$ V with $V_{EE} = -4.2$ V to -5.7 V
- Internal Input Pulldown Resistors on D and CLK
- Meets or Exceeds JEDEC Spec EIA/JESD78 IC Latchup Test
- Moisture Sensitivity:
    - ♦ Level 1 for SOIC−8 NB
    - ♦ For Additional Information, see Application Note AND8003/D
- Flammability Rating: UL 94 V−0 @ 0.125 in, Oxygen: Index 28 to 34
- Transistor Count = 48 Devices
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

MARKING DIAGRAM
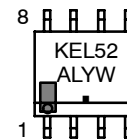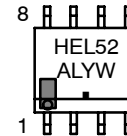
8
HEL52
ALYW
1

8
KEL52
ALYW
1

H = MC10
K = MC100
A = Assembly Location
L = Wafer Lot

Y = Year
W = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)
*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

Device	Package	Shipping
MC10EL52DG	SOIC−8NB (Pb-Free)	98 Units/Tube

DISCONTINUED (Note 1)

MC10EL52DR2G	SOIC−8 NB (Pb-Free)	2,500 Tape & Reel
MC100EL52DG	SOIC−8 NB (Pb-Free)	98 Units/Tube

1. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.
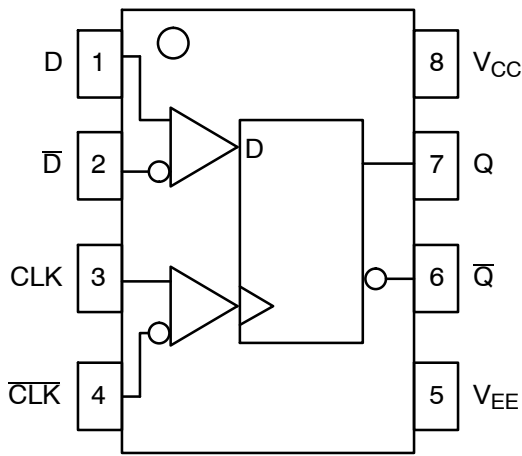
MC10EL52, MC100EL52

Figure 1. Logic Diagram and Pinout Assignment

Table 1. TRUTH TABLE

D*	CLK*	Q
L H	Z Z	L H

Z = LOW to HIGH Transition

* Pin will default low when left open.

Table 2. PIN DESCRIPTION

PIN	FUNCTION
D, $\overline{D}$	ECL Data Input
CLK, $\overline{CLK}$	ECL Clock Input
Q, $\overline{Q}$	ECL Data Output
V_{CC}	Positive Supply
V_{EE}	Negative Supply

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	PECL Mode Power Supply	$V_{EE} = 0$ V		8	V
V_{EE}	NECL Mode Power Supply	$V_{CC} = 0$ V		−8	V
V_I	PECL Mode Input Voltage NECL Mode Input Voltage	$V_{EE} = 0$ V $V_{CC} = 0$ V	$V_I \leq V_{CC}$ $V_I \geq V_{EE}$	6 −6	V
I_{out}	Output Current	Continuous Surge		50 100	mA
T_A	Operating Temperature Range			−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC−8 NB SOIC−8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC−8 NB	41 to 44	°C/W
T_{sol}	Wave Solder (Pb-Free)	< 2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 4. 10EL SERIES PECL DC CHARACTERISTICS (V_{CC} = 5.0 V; V_{EE} = 0 V (Note 2))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current		21	25		21	25		21	25	mA
V_{OH}	Output HIGH Voltage (Note 2)	3920	4010	4110	4020	4105	4190	4090	4185	4280	mV
V_{OL}	Output LOW Voltage (Note 3)	3050	3200	3350	3050	3210	3370	3050	3227	3405	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	3770		4110	3870		4190	3940		4280	mV
V_{IL}	Input LOW Voltage (Single-Ended)	3050		3500	3050		3520	3050		3555	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4) D CLK	3.4 2.5		4.6 4.4	3.4 2.5		4.6 4.4	3.4 2.5		4.6 4.4	V
I_{IH}	Input HIGH Current			150			150			150	µA
I_{IL}	Input LOW Current	0.5			0.5			0.3			µA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

2. Input and output parameters vary 1:1 with V_{CC}.
   V_{EE} can vary +0.25 V / −0.5 V for +25°C. or +85°C. or V_{EE} can vary +0.06 V / −0.5 V for −40°C.
3. Outputs are terminated through a 50 ohm resistor to V_{CC} − 2.0 V.
4. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

Table 5. 10EL SERIES NECL DC CHARACTERISTICS (V_{CC} = 0 V; V_{EE} = −5.0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current		21	25		21	25		21	25	mA
V_{OH}	Output HIGH Voltage (Note 2)	−1080	−990	−890	−980	−895	−810	−910	−815	−720	mV
V_{OL}	Output LOW Voltage (Note 2)	−1950	−1800	−1650	−1950	−1790	−1630	−1950	−1773	−1595	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	−1230		−890	−1130		−810	−1060		−720	mV
V_{IL}	Input LOW Voltage (Single-Ended)	−1950		−1500	−1950		−1480	−1950		−1445	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4) D CLK	−1.6 −2.5		−0.4 −0.6	−1.6 −2.5		−0.4 −0.6	−1.6 −2.5		−0.4 −0.6	V
I_{IH}	Input HIGH Current			150			150			150	µA
I_{IL}	Input LOW Current	0.5			0.5			0.3			µA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V_{CC}.
   V_{EE} can vary +0.25 V / −0.5 V for +25°C. or +85°C. or V_{EE} can vary +0.06 V / −0.5 V for −40°C.
2. Outputs are terminated through a 50 ohm resistor to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

MC10EL52, MC100EL52

Table 6. 100EL SERIES PECL DC CHARACTERISTICS (V_{CC} = 5.0 V; V_{EE} = 0 V (Note 1))

Symbol	Characteristic	−40°C Min	−40°C Typ	−40°C Max	25°C Min	25°C Typ	25°C Max	85°C Min	85°C Typ	85°C Max	Unit
I_{EE}	Power Supply Current		21	25		21	25		24	29	mA
V_{OH}	Output HIGH Voltage (Note 2)	3915	3995	4120	3975	4045	4120	3975	4050	4120	mV
V_{OL}	Output LOW Voltage (Note 2)	3170	3305	3445	3190	3295	3380	3190	3295	3380	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	3835		4120	3835		4120	3835		4120	mV
V_{IL}	Input LOW Voltage (Single-Ended)	3190		3525	3190		3525	3190		3525	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4) D CLK	2.6 2.5		4.6 4.2	2.6 2.5		4.6 4.2	2.6 2.5		4.6 4.2	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.
1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.8 V / −0.5 V.
2. Outputs are terminated through a 50 ohm resistor to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

Table 7. 100EL SERIES NECL DC CHARACTERISTICS (V_{CC} = 0 V; V_{EE} = −5.0 V (Note 1))

Symbol	Characteristic	−40°C Min	−40°C Typ	−40°C Max	25°C Min	25°C Typ	25°C Max	85°C Min	85°C Typ	85°C Max	Unit
I_{EE}	Power Supply Current		21	25		21	25		24	29	mA
V_{OH}	Output HIGH Voltage (Note 2)	−1085	−1005	−880	−1025	−955	−880	−1025	−955	−880	mV
V_{OL}	Output LOW Voltage (Note 2)	−1830	−1695	−1555	−1810	−1705	−1620	−1810	−1705	−1620	mV
V_{IH}	Input HIGH Voltage (Single-Ended)	−1165		−880	−1165		−880	−1165		−880	mV
V_{IL}	Input LOW Voltage (Single-Ended)	−1810		−1475	−1810		−1475	−1810		−1475	mV
V_{IHCMR}	Input HIGH Voltage Common Mode Range (Differential Configuration) (Note 4) D CLK	−2.4 −2.5		−0.4 −0.8	−2.4 −2.5		−0.4 −0.8	−2.4 −2.5		−0.4 −0.8	V
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.
1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.8 V / −0.5 V.
2. Outputs are terminated through a 50 ohm resistor to V_{CC} − 2.0 V.
3. V_{IHCMR} min varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between V_{PP}min and 1 V.

Table 8. AC CHARACTERISTICS (V_{CC} = 5.0 V; V_{EE} = 0 V or V_{CC} = 0 V; V_{EE} = −5.0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
fmax	Maximum Toggle Frequency	1.8	2.5		2.2	2.8		2.2	2.8		GHz
t_{PLH} t_{PHL}	Propagation Delay to Output CLK	225	335	515	275	365	465	320	410	510	ps
t_S	Setup Time	125	0		125	0		125	0		ps
t_H	Hold Time	150	50		150	50		150	50		ps
t_{PW}	Minimum Pulse Width	400			400			400			ps
V_{PP}	Input Swing (Note 2)	150		1000	150		1000	150		1000	mV
t_{JITTER}	Cycle-to-Cycle Jitter		TBD			TBD			TBD		ps
t_r t_f	Output Rise/Fall Times Q (20%−80%)	100	225	350	100	225	350	100	225	350	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. 10 Series: V_{EE} can vary +0.25 V / −0.5 V for +25°C and +85°C. or V_{EE} can vary +0.06 V / −0.5 V for −40°C
   100 Series: V_{EE} can vary +0.8 V / −0.5 V.
2. V_{PP}(min) is minimum input swing for which AC parameters guaranteed. The device has a DC gain of ≈40.
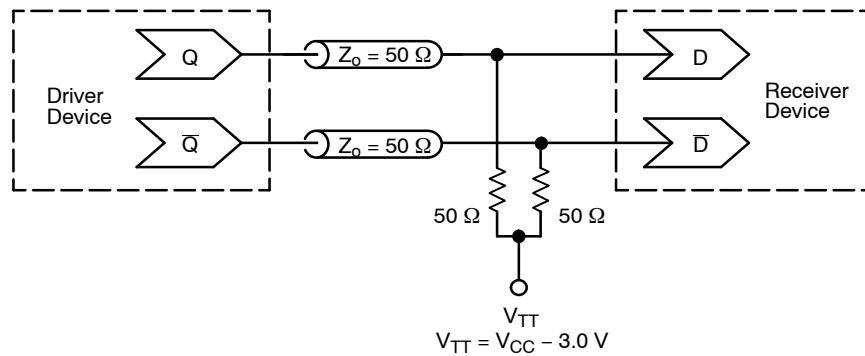
Figure 2. Typical Termination for Output Driver and Device Evaluation
(See Application Note AND8020/D – Termination of ECL Logic Devices)

Resource Reference of Application Notes

AN1405/D   –   ECL Clock Distribution Techniques

AN1406/D   –   Designing with PECL (ECL at +5.0 V)

AN1503/D   –   ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D   –   Metastability and the ECLinPS Family

AN1568/D   –   Interfacing Between LVDS and ECL

AN1672/D   –   The ECL Translator Guide

AND8001/D   –   Odd Number Counters Design

AND8002/D   –   Marking and Date Codes

AND8020/D   –   Termination of ECL Logic Devices

AND8066/D   –   Interfacing with ECLinPS

AND8090/D   –   AC Characteristics of ECL Devices

SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

8

1

SCALE 1:1

−X−

A

B

8   5

S

1   4

−Y−

G

⊕ | 0.25 (0.010) Ⓜ | Y | Ⓜ

C

SEATING
PLANE

−Z−

◁ | 0.10 (0.004)

H

D

⊕ | 0.25 (0.010)Ⓜ | Z | Y Ⓢ | X Ⓢ

K

N X 45°

M   J

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC
MARKING DIAGRAM*

SOLDERING FOOTPRINT*

1.52
0.060

7.0
0.275

4.0
0.155

0.6
0.024

1.270
0.050

SCALE 6:1   (mm / inches)

8   XXXXX ALYWX   1

IC

8   XXXXX ALYWX   1

IC
(Pb−Free)

8   XXXXXX AYWW   1

Discrete

8   XXXXXX AYWW   1

Discrete
(Pb−Free)

XXXXX = Specific Device Code
A   = Assembly Location
L   = Wafer Lot
Y   = Year
W   = Work Week
▪   = Pb−Free Package

XXXXXX = Specific Device Code
A   = Assembly Location
Y   = Year
WW   = Work Week
▪   = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

STYLE 1:
PIN 1. EMITTER
   2. COLLECTOR
   3. COLLECTOR
   4. EMITTER
   5. EMITTER
   6. BASE
   7. BASE
   8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
   2. COLLECTOR, #1
   3. COLLECTOR, #2
   4. COLLECTOR, #2
   5. BASE, #2
   6. EMITTER, #2
   7. BASE, #1
   8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
   2. DRAIN, #1
   3. DRAIN, #2
   4. DRAIN, #2
   5. GATE, #2
   6. SOURCE, #2
   7. GATE, #1
   8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
   2. ANODE
   3. ANODE
   4. ANODE
   5. ANODE
   6. ANODE
   7. ANODE
   8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
   2. DRAIN
   3. DRAIN
   4. DRAIN
   5. GATE
   6. GATE
   7. SOURCE
   8. SOURCE

STYLE 6:
PIN 1. SOURCE
   2. DRAIN
   3. DRAIN
   4. SOURCE
   5. SOURCE
   6. GATE
   7. GATE
   8. SOURCE

STYLE 7:
PIN 1. INPUT
   2. EXTERNAL BYPASS
   3. THIRD STAGE SOURCE
   4. GROUND
   5. DRAIN
   6. GATE 3
   7. SECOND STAGE Vd
   8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
   2. BASE, #1
   3. BASE, #2
   4. COLLECTOR, #2
   5. COLLECTOR, #2
   6. EMITTER, #2
   7. EMITTER, #1
   8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
   2. COLLECTOR, DIE #1
   3. COLLECTOR, DIE #2
   4. EMITTER, COMMON
   5. EMITTER, COMMON
   6. BASE, DIE #2
   7. BASE, DIE #1
   8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
   2. BIAS 1
   3. OUTPUT
   4. GROUND
   5. GROUND
   6. BIAS 2
   7. INPUT
   8. GROUND

STYLE 11:
PIN 1. SOURCE 1
   2. GATE 1
   3. SOURCE 2
   4. GATE 2
   5. DRAIN 2
   6. DRAIN 2
   7. DRAIN 1
   8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
   2. SOURCE
   3. SOURCE
   4. GATE
   5. DRAIN
   6. DRAIN
   7. DRAIN
   8. DRAIN

STYLE 13:
PIN 1. N.C.
   2. SOURCE
   3. SOURCE
   4. GATE
   5. DRAIN
   6. DRAIN
   7. DRAIN
   8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
   2. N−GATE
   3. P−SOURCE
   4. P−GATE
   5. P−DRAIN
   6. P−DRAIN
   7. N−DRAIN
   8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
   2. ANODE 1
   3. ANODE 1
   4. ANODE 1
   5. CATHODE, COMMON
   6. CATHODE, COMMON
   7. CATHODE, COMMON
   8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
   2. BASE, DIE #1
   3. EMITTER, DIE #2
   4. BASE, DIE #2
   5. COLLECTOR, DIE #2
   6. COLLECTOR, DIE #2
   7. COLLECTOR, DIE #1
   8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
   2. V2OUT
   3. V1OUT
   4. TXE
   5. RXE
   6. VEE
   7. GND
   8. ACC

STYLE 18:
PIN 1. ANODE
   2. ANODE
   3. SOURCE
   4. GATE
   5. DRAIN
   6. DRAIN
   7. CATHODE
   8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
   2. GATE 1
   3. SOURCE 2
   4. GATE 2
   5. DRAIN 2
   6. MIRROR 2
   7. DRAIN 1
   8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
   2. GATE (N)
   3. SOURCE (P)
   4. GATE (P)
   5. DRAIN
   6. DRAIN
   7. DRAIN
   8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
   2. CATHODE 2
   3. CATHODE 3
   4. CATHODE 4
   5. CATHODE 5
   6. COMMON ANODE
   7. COMMON ANODE
   8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
   2. COMMON CATHODE/VCC
   3. COMMON CATHODE/VCC
   4. I/O LINE 3
   5. COMMON ANODE/GND
   6. I/O LINE 4
   7. I/O LINE 5
   8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
   2. COMMON ANODE/GND
   3. COMMON ANODE/GND
   4. LINE 2 IN
   5. LINE 2 OUT
   6. COMMON ANODE/GND
   7. COMMON ANODE/GND
   8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
   2. EMITTER
   3. COLLECTOR/ANODE
   4. COLLECTOR/ANODE
   5. CATHODE
   6. CATHODE
   7. COLLECTOR/ANODE
   8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
   2. N/C
   3. REXT
   4. GND
   5. IOUT
   6. IOUT
   7. IOUT
   8. IOUT

STYLE 26:
PIN 1. GND
   2. dv/dt
   3. ENABLE
   4. ILIMIT
   5. SOURCE
   6. SOURCE
   7. SOURCE
   8. VCC

STYLE 27:
PIN 1. ILIMIT
   2. OVLO
   3. UVLO
   4. INPUT+
   5. SOURCE
   6. SOURCE
   7. SOURCE
   8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
   2. DASIC_OFF
   3. DASIC_SW_DET
   4. GND
   5. V_MON
   6. VBULK
   7. VBULK
   8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
   2. EMITTER, #1
   3. BASE, #2
   4. EMITTER, #2
   5. COLLECTOR, #2
   6. COLLECTOR, #2
   7. COLLECTOR, #1
   8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
   2. DRAIN 1
   3. GATE 2
   4. SOURCE 2
   5. SOURCE 1/DRAIN 2
   6. SOURCE 1/DRAIN 2
   7. SOURCE 1/DRAIN 2
   8. GATE 1

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DESCRIPTION:	SOIC−8 NB		PAGE 2 OF 2

ADDITIONAL INFORMATION

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